

Abstract of the Disclosure

A method is provided for forming a silicon dioxide film using atomic layer deposition (ALD), wherein a halogen- or NCO- substituted siloxane is used as a Si source. The method includes feeding a substituted siloxane as a first reactant onto a substrate to form a chemisorbed layer of the first reactant, and thereafter feeding a compound consisting of oxygen and hydrogen as a second reactant onto the chemisorbed layer to form the desired silicon dioxide film.

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